

CD40106B

CMOS Hex Schmitt Triggers High-Voltage Types (20-Volt Rating)

CD40106B consists of six Schmitt trigger circuits. Each circuit functions as an inverter with Schmitt trigger action on the input. The trigger switches at different points for positive and negative-going signals. The difference between the positive-going voltage (V_P) and the negative-going voltage (V_N) is defined as hysteresis voltage (V_H) (see Fig.2).

The CD40106B types are supplied in 14 lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic package (E suffix), and in chip form (H suffix).

Features:

- Schmitt-trigger action with no external components
- Hysteresis voltage (typ.) 0.9V at $V_{DD}=5V$, 2.3V at $V_{DD}=10V$, and 3.5V at $V_{DD}=15V$
- Noise immunity greater than 50%
- No limit on input rise and fall times
- Standardized, symmetrical output characteristics
- 100% tested for quiescent current at 20V
- Maximum input current of 1 μ A at 18V over full package-temperature range; 100nA at 18V and 25 $^{\circ}$ C
- Low V_{DD} to V_{SS} current during slow input ramp
- 5V, 10V, and 15V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

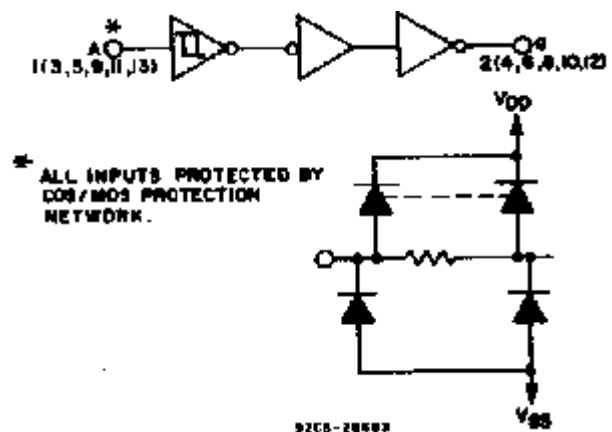
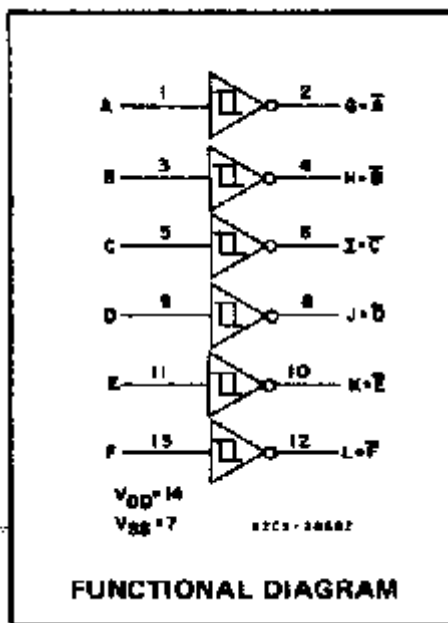


Fig.1-Logic diagram (1 of 6 Schmitt triggers)

Applications:

- Wave and pulse shapers
- High-noise-environment systems
- Monostable multivibrators
- Astable multivibrators

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})	-0.5V to +20V
Voltage referenced to V_{SS} Terminal	
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5V to $V_{DD} + 0.5V$
DC INPUT CURRENT, ANY ONE INPUT	$\pm 10mA$
POWER DISSIPATION PER PACKAGE (P_D):	
For $T_A = -55^\circ C$ to $+100^\circ C$	500mW
For $T_A = +100^\circ C$ to $+125^\circ C$	Derate Linearity at 12mW/ $^\circ C$ to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE}$ (All Package Types)	100mW
OPERATING-TEMPERATURE RANGE (T_A)	$-55^\circ C$ to $+125^\circ C$
STORAGE TEMPERATURE RANGE (T_{stg})	$-65^\circ C$ to $+150^\circ C$
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ inch ($1.59 \pm 0.79mm$) from case for 10s max	$+265^\circ C$

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A Full Package Temperature Range)	3	18	V

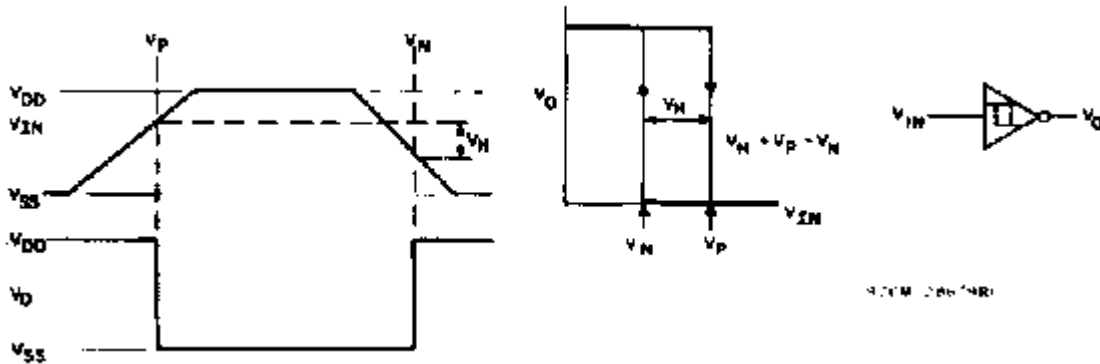
DYNAMIC ELECTRICAL CHARACTERISTICS

At $T_A = 25^\circ C$, Input $t_r, t_f = 20ns$, $C_L = 50pF$, $R_L = 200k\Omega$

CHARACTERISTIC	TEST CONDITIONS	LIMITS		UNITS	
		V_{DD} (V)	TYP		MAX.
Propagation Delay Time: t_{PHL} t_{PLH}		5	140	280	ns
		10	70	140	
		15	60	120	
Transition Time: t_{THL} t_{TLH}		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C_{iN}	Any Input		5	7.5	pF

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS	
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55	-40	+85	+125	+25				
								Min.	Typ.	Max.		
Quiescent Device Current, I _{DD} Max.	-	0,5	5	1	1	30	30	-	0.02	1	μA	
	-	0,10	10	2	2	60	60	-	0.02	2		
	-	0,15	15	4	4	120	120	-	0.02	4		
	-	0,20	20	20	20	600	600	-	0.04	20		
Positive Trigger Threshold Voltage V _P Min.	-	-	5	2.2	2.2	2.2	2.2	2.2	2.9	-	V	
	-	-	10	4.6	4.6	4.6	4.6	4.6	5.9	-		
	-	-	15	6.8	6.8	6.8	6.8	6.8	8.8	-		
	V _P Max.	-	-	5	3.6	3.6	3.6	3.6	-	2.9		3.6
		-	-	10	7.1	7.1	7.1	7.1	-	5.9		7.1
		-	-	15	10.8	10.8	10.8	10.8	-	8.8		10.8
Negative Trigger Threshold Voltage V _N Min.	-	-	5	0.9	0.9	0.9	0.9	0.9	1.9	-	V	
	-	-	10	2.5	2.5	2.5	2.5	2.5	3.9	-		
	-	-	15	4	4	4	4	4	5.8	-		
	V _N Max.	-	-	5	2.8	2.8	2.8	2.8	-	1.9		2.8
		-	-	10	5.2	5.2	5.2	5.2	-	3.9		5.2
		-	-	15	7.4	7.4	7.4	7.4	-	5.8		7.4
Hysteresis Voltage V _H Min.	-	-	5	0.3	0.3	0.3	0.3	0.3	0.9	-	V	
	-	-	10	1.2	1.2	1.2	1.2	1.2	2.3	-		
	-	-	15	1.6	1.6	1.6	1.6	1.6	3.5	-		
	V _H Max.	-	-	5	1.6	1.6	1.6	1.6	-	0.9		1.6
		-	-	10	3.4	3.4	3.4	3.4	-	2.3		3.4
		-	-	15	5	5	5	5	-	3.5		5
Output Low (Sink) Current, I _{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	-	mA	
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-		
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	-		
Output High (Source) Current, I _{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-		
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-		
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-		
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-		
Output Voltage Low-Level, V _{OL} Max.	-	5	5	0.05				-	0	0.05		V
	-	10	10	0.05				-	0	0.05		
	-	15	15	0.05				-	0	0.05		
Output Voltage High Level, V _{OH} Min.	-	0	5	4.95				4.95	5	-		
	-	0	10	9.95				9.95	10	-		
	-	0	15	14.95				14.95	15	-		
Input Current, I _{IN} Max.	-	0,18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μA	



a) Definition of V_p, V_N, V_H b) Transfer characteristics of 1 of 6 gates
 Fig.2-Hysteresis definition, characteristics, and test set-up

APPLICATIONS

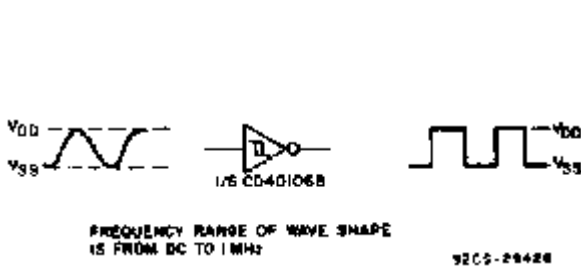


Fig.3-Wave shaper

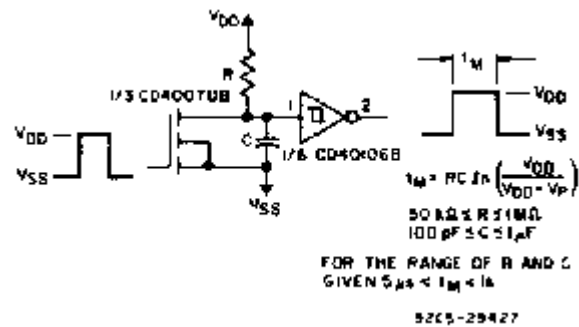


Fig.4-Monostable multivibrator

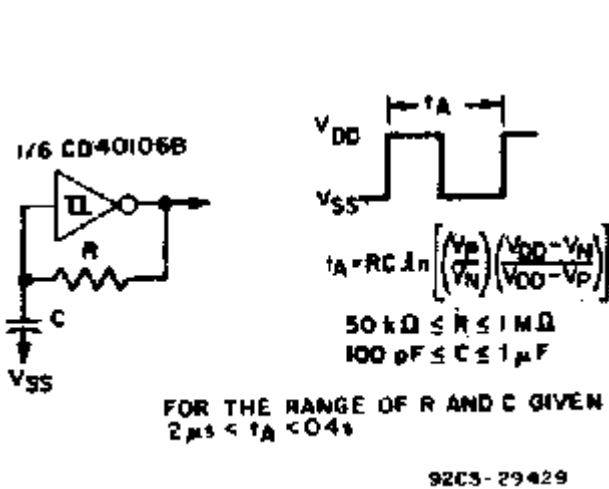


Fig.5-Astable multivibrator

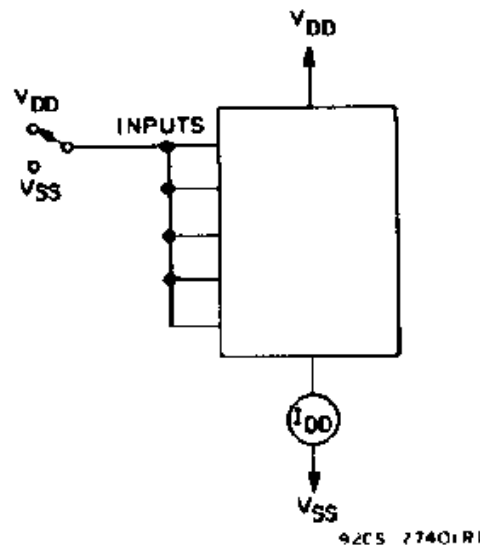


Fig.6-Quiescent device current test circuit

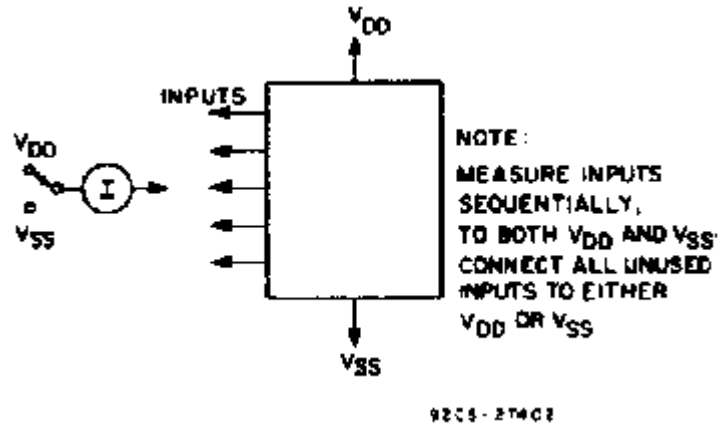


Fig.7-Input current test circuit

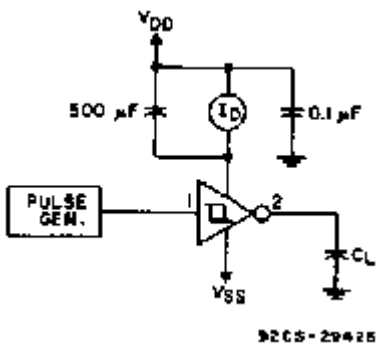


Fig.8-Dynamic power dissipation test circuit

